a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region; and

a second conductive layer formed on said first conductive layer,

wherein said first conductive layer comprises tantalum and said second layer comprises aluminum, and

wherein said first conductive layer is thinner than said second conductive layer.

6. (Amended) A semiconductor device comprising:

a semiconductor layer having at least a channel region formed on an insulating surface;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region; and

a second conductive layer formed on said first conductive layer wherein said second conductive layer comprises a different material from said first conductive layer,

wherein each of said first and second conductive layers comprises a material selected from the group consisting of

molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt, and

wherein said first conductive laver is thinner than said second conductive laver.

11. (Amended) A semiconductor device comprising:

a semiconductor layer having at least a channel region formed on an insulating surface;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region; and

a second conductive layer electrically connected to said first conductive layer,

wherein said first conductive layer comprises tantalum and said second layer comprises aluminum, and

wherein said first conductive layer is thinner than said second conductive layer.

16. (Amended) A semiconductor device comprising:

a semiconductor layer having at least a channel region formed on an insulating surface;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region; and

a second conductive layer electrically connected to said first conductive layer wherein said second conductive layer comprises a different material from said first conductive layer,

wherein each of said first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt, and

wherein said first conductive laver is thinner than said second conductive layer.

Please add the following new claims.

--21. (New) A semiconductor device comprising:

a gate electrode comprising a first layer and a second layer formed on an insulating surface;

an insulating film formed on said gate electrode;

a semiconductor layer having at least a channel region formed on said insulating film,

wherein said first layer and said second layer comprises a material selected from the group consisting of molybdenum,

tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt, and

wherein said first layer is thinner than said second layer.

22. (New) A semiconductor device according to claim 21, wherein said insulating film comprises silicon oxide.

23. (New) A semiconductor device according to claim 21, wherein said semiconductor layer comprises polysilicon.

24. (New) A semiconductor device according to claim 21, further comprising a pair of impurity regions in said semiconductor layer with said channel region interposed therebetween.

25. (New) A semiconductor device comprising:

a gate electrode comprising a first layer and a second layer formed on an insulating surface;

an insulating film formed on said gate electrode;

a semiconductor layer having at least a channel region formed on said insulating film;

an oxide film formed on at least side surfaces of said gate electrode, said oxide film comprises an oxide of a material of said gate electrode,

wherein said first layer and said second layer comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt, and

wherein said first layer is thinner than said second layer.

26. (New) A semiconductor device according to claim 25, wherein said insulating film comprises silicon oxide.

27. (New) A semiconductor device according to claim 25, wherein said semiconductor layer comprises polysilicon.

28. (New) A semiconductor device according to claim 25, further comprising a pair of impurity regions said semiconductor layer with said channel region interposed therebetween.

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested.

Claims 4, 9, 14, and 19 are canceled and claims 1, 6, 11 and 16 have been amended to include the limitations that the first conductive layer is thinner than the second conductive layer. In some embodiments, that first conductive layer is tantalum, and the second conductive layer is aluminum.